

INTRODUCE:

HVGT high voltage silicon rectifier diodes is made of high quality silicon wafer chip and high reliability epoxy resin sealing structure, and through professional testing equipment inspection qualified after to customers.

FEATURES:

1. High overload surge capability.
2. High Current,Low Forward Voltage.
3. Avalanche Characteristic.
4. Conform to RoHS and SGS.
5. Epoxy resin molded in vacuumHave anticorrosion in the surface.

APPLICATIONS:

1. High voltage power supply rectifier.
2. High voltage rectifier circuit for microwave oven.
3. Other.

MECHANICAL DATA:

1. Case: epoxy resin molding.
2. Terminal: welding axis.
3. Net weight: 2.50 grams (approx).

SHAPE DISPLAY:

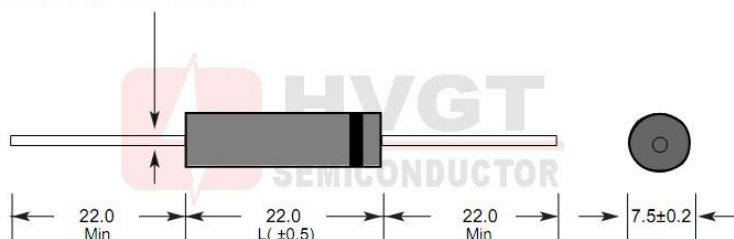
Part Marking:
Code:

**CL01-16
HVGT**

Cathode Mark:

SIZE: (Unit:mm)
HVGT NAME: DO-722
DO-722 Series

Lead Diameter 1.2mm ±0.02



Unit:mm

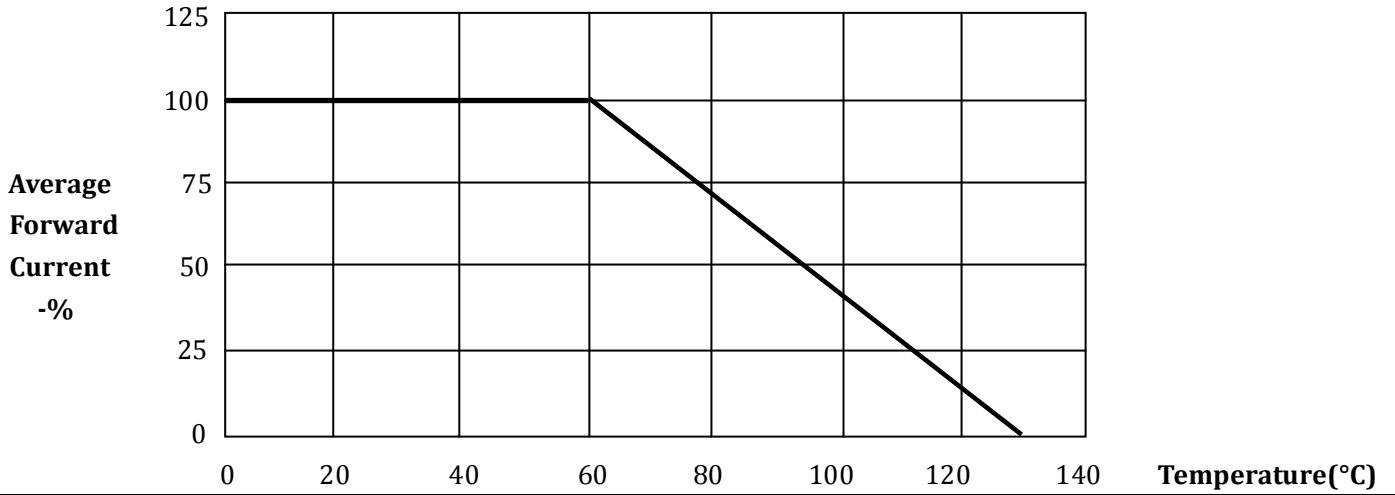
MAXIMUM RATINGS AND CHARACTERISTICS: Ta=25°C (Absolute Maximum Ratings)

Items	Symbols	Condition	Data Value	Units
Repetitive Peak Reverse Voltage	V_{RRM}		16	kV
Average Forward Current Maximum	I_{FAVM}	60Hz Half-Sine Wave, Resistance Load, $T_a=60^\circ\text{C}$	350	mA
Non-Repetitive Forward Surge Current	I_{FSM}	60Hz Half-Sine Wave; 8.3ms; 1Cycle	30	A
Reverse surge current	I_{RSM}	$W_P=1\text{ms}$, Rectangular-Wave, One-shot,	100	mA
Junction Temperature	T_j		130	°C
Allowable Operation Case Temperature	T_c		-40~+130	°C
Storage Temperature	T_{STG}		-40~+130	°C

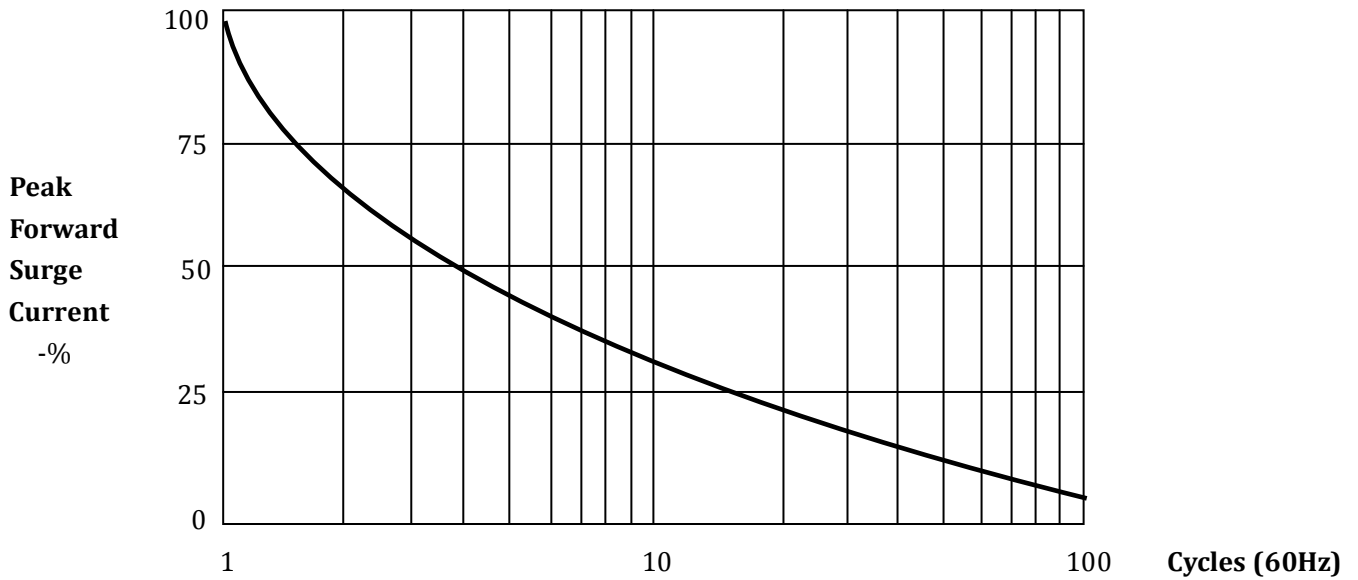
ELECTRICAL CHARACTERISTICS: Ta=25°C (Unless Otherwise Specified)

Items	Symbols	Condition	Data value	Units
Maximum Forward Voltage Drop	V_{FM}	at 25°C; at I_{FAVM}	14	V
Maximum Reverse Current	I_{R1}	at 25°C; at V_{RRM}	5.0	uA
	I_{R2}	at 100°C; at V_{RRM}	50	uA
Maximum Reverse Recovery Time	T_{RR}	at 25°C; $I_F=0.5I_R$; $I_R=I_{FAVM}$; $I_{RR}=0.25I_R$	--	nS
Reverse Breakdown Voltage	V_Z	at 25°C; $I_R=100\text{uA}$	16.5	kV

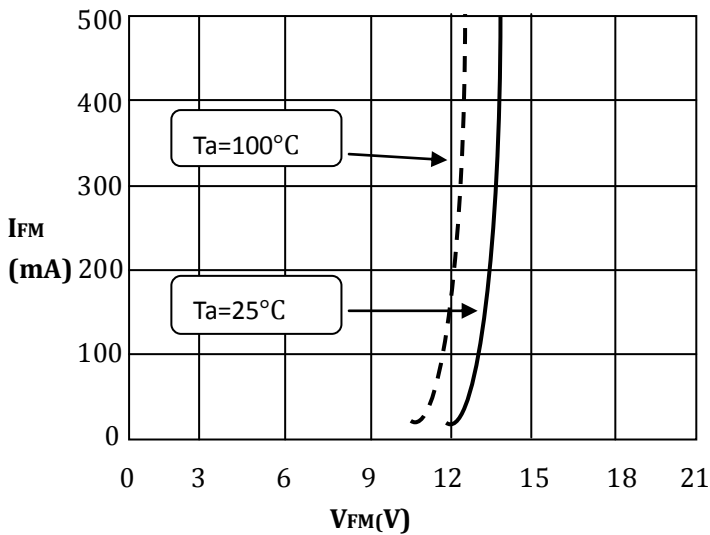
Forward Current Derating Curves



Non-Repetitive Surge Current



Forward Characteristics



Reverse Characteristics

